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(54) **ADJUSTED FIN WIDTH IN INTEGRATED CIRCUITRY**

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See application file for complete search history.

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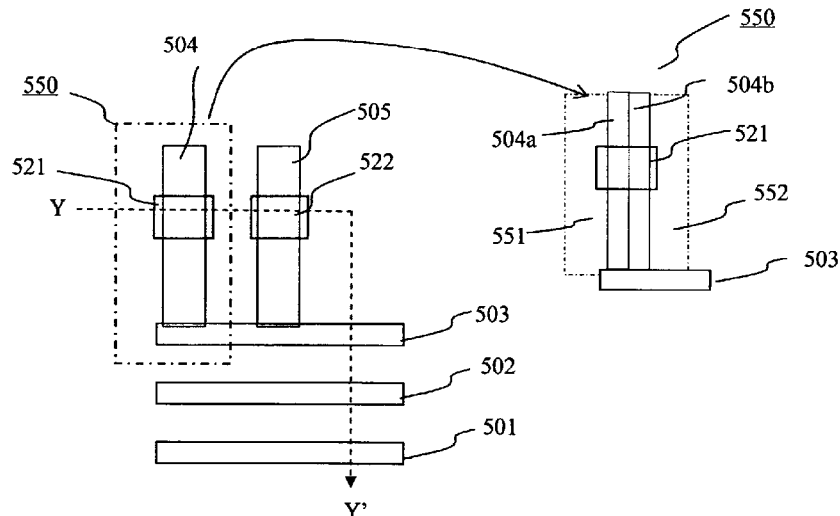
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(57) **ABSTRACT**

A method includes growing a plurality of parallel mandrels on a surface of a semiconductor substrate, each mandrel having at least two laterally opposite sidewalls and a predetermined width. The method further includes forming a first type of spacers on the sidewalls of the mandrels, wherein the first type of spacers between two adjacent mandrels are separated by a gap. The predetermined mandrel width is adjusted to close the gap between the adjacent first type of spacers to form a second type of spacers. The mandrels are removed to form a first type of fins from the first type of spacers, and to form a second type of fins from spacers between two adjacent mandrels. The second type of fins are wider than the first type of fins.

6 Claims, 13 Drawing Sheets



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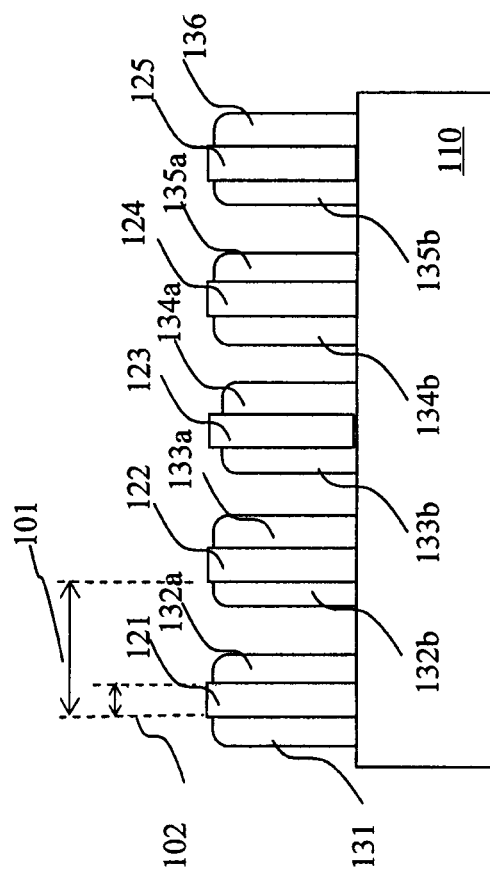


FIG. 1A

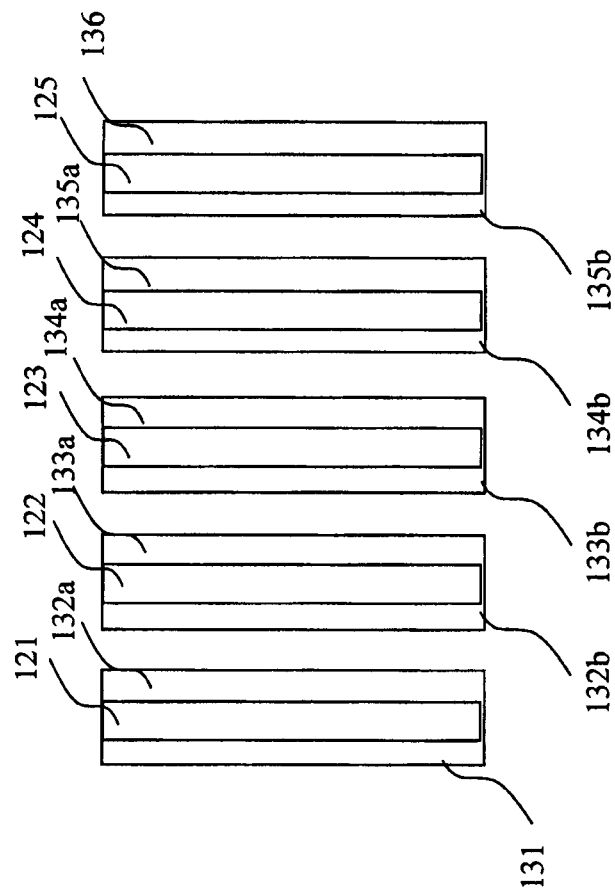


FIG. 1B

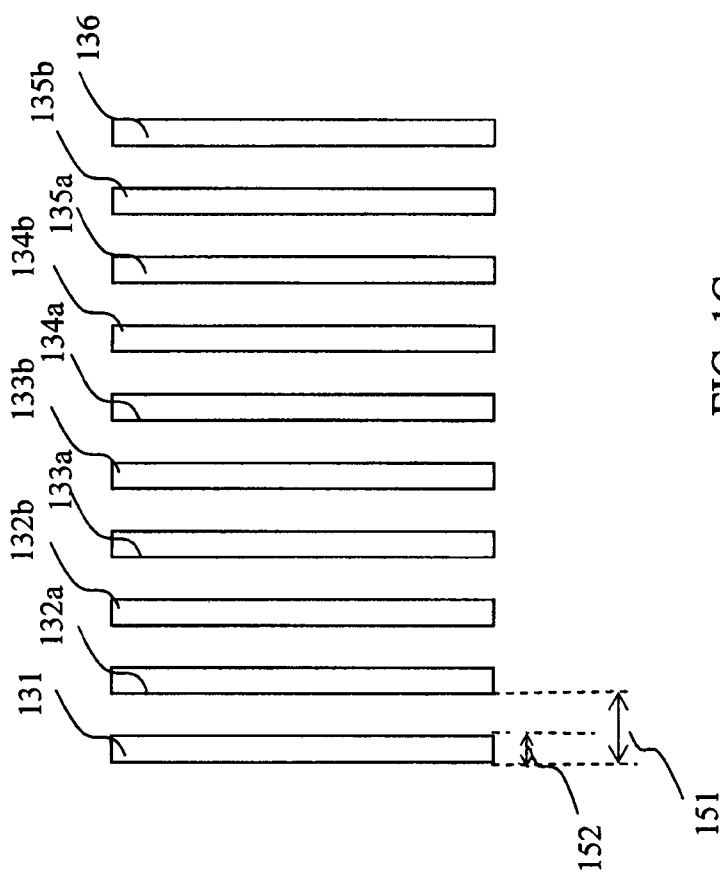


FIG. 1C

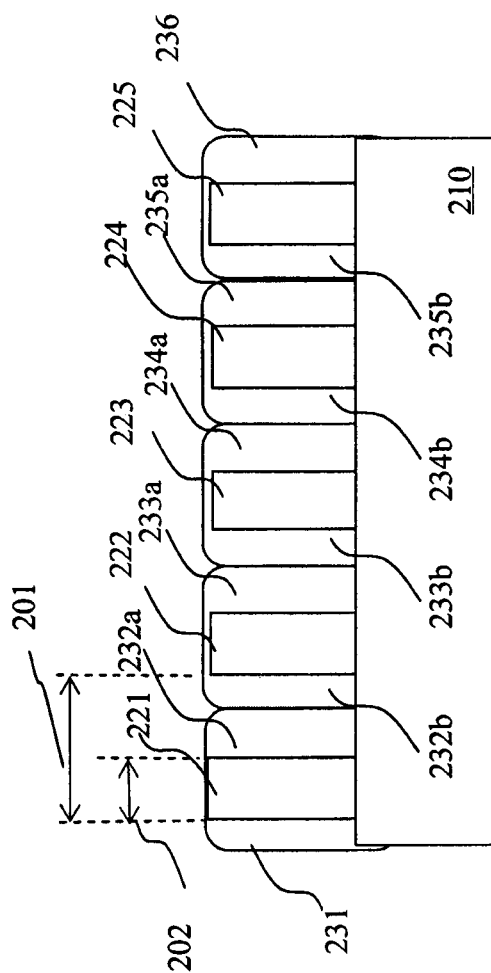


FIG. 2A

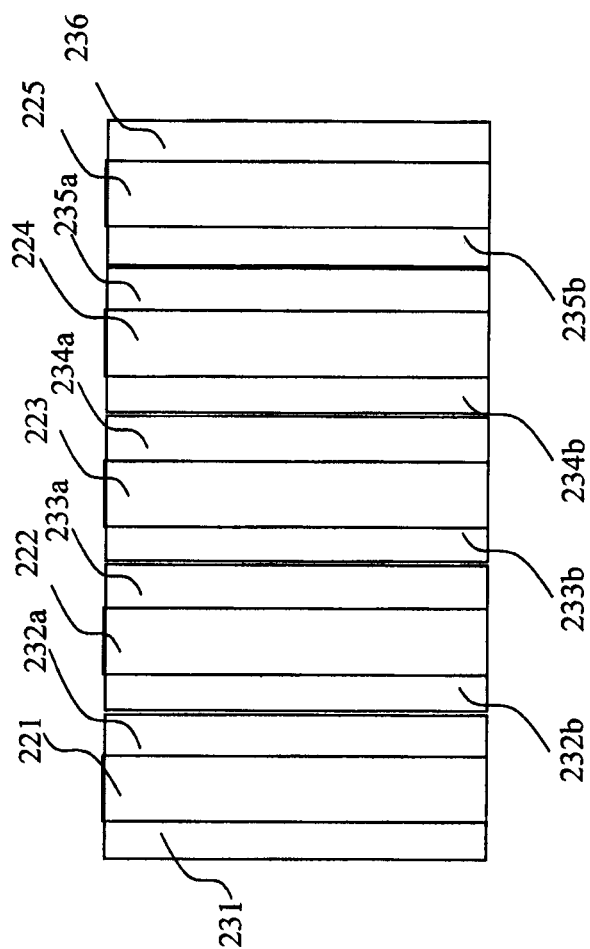


FIG. 2B

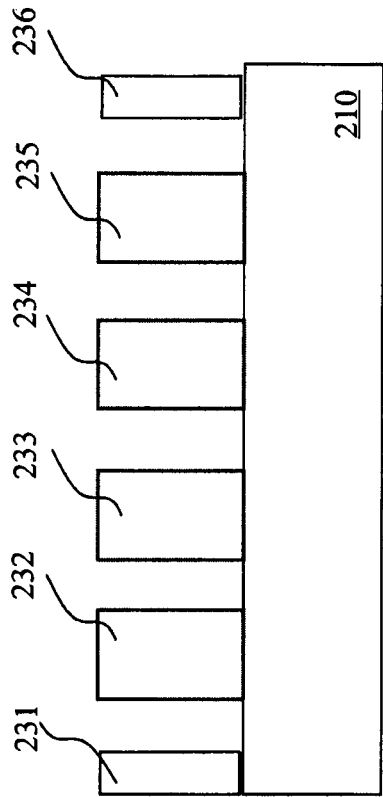


FIG. 3A

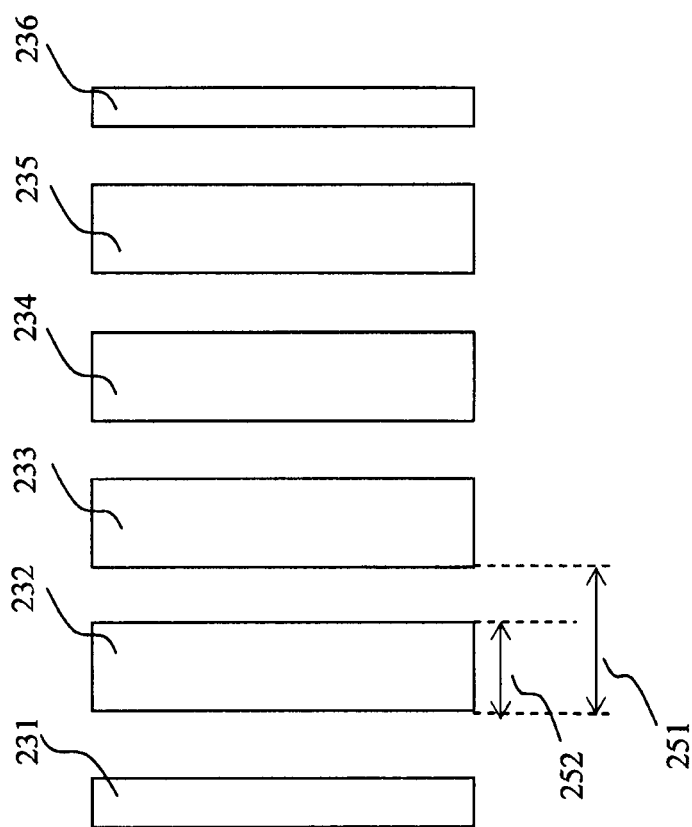


FIG. 3B

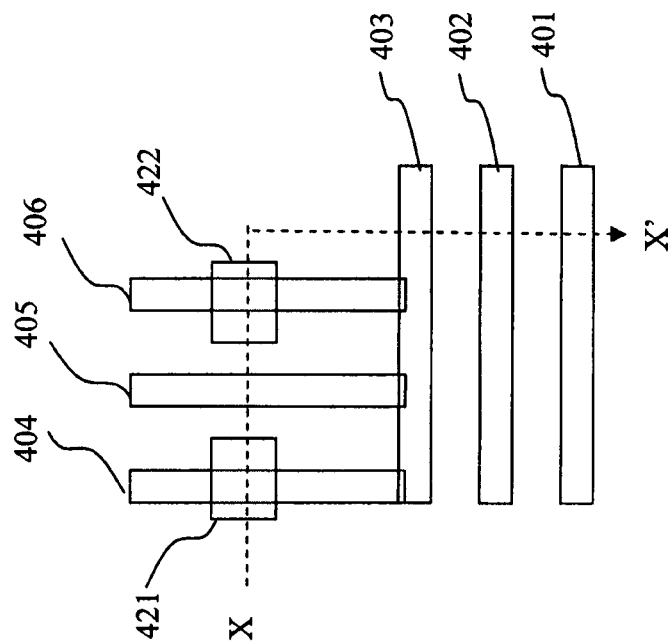


FIG. 4A

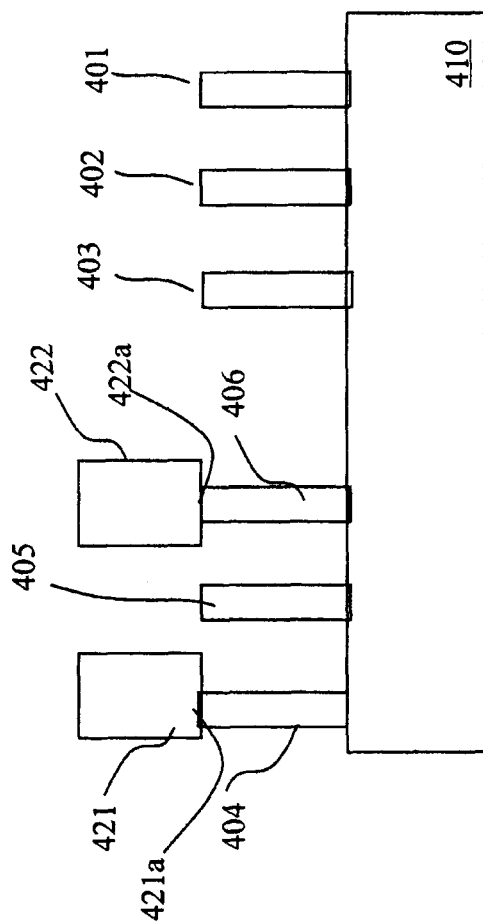


FIG. 4B

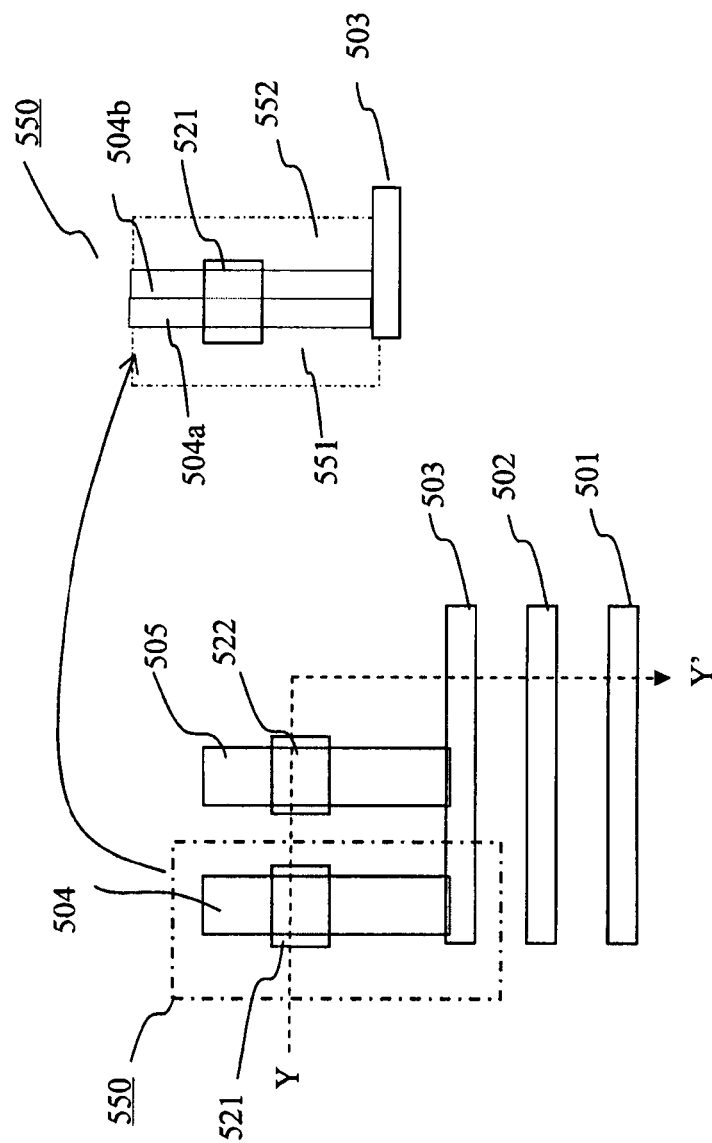


FIG. 5A

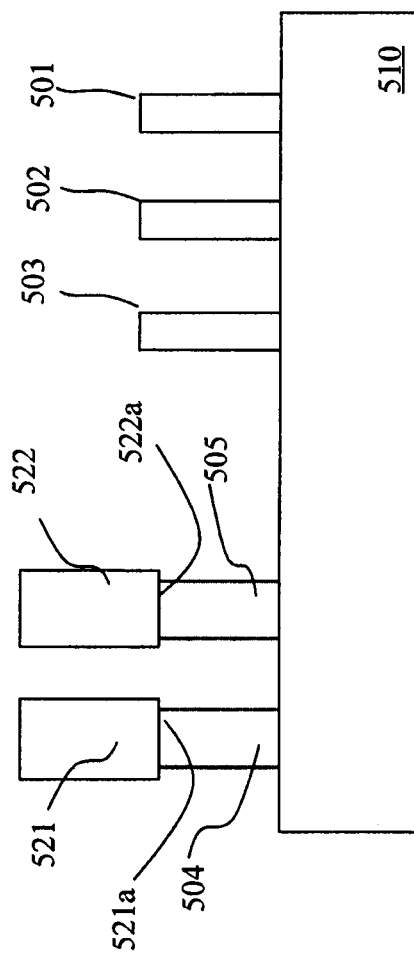


FIG. 5B

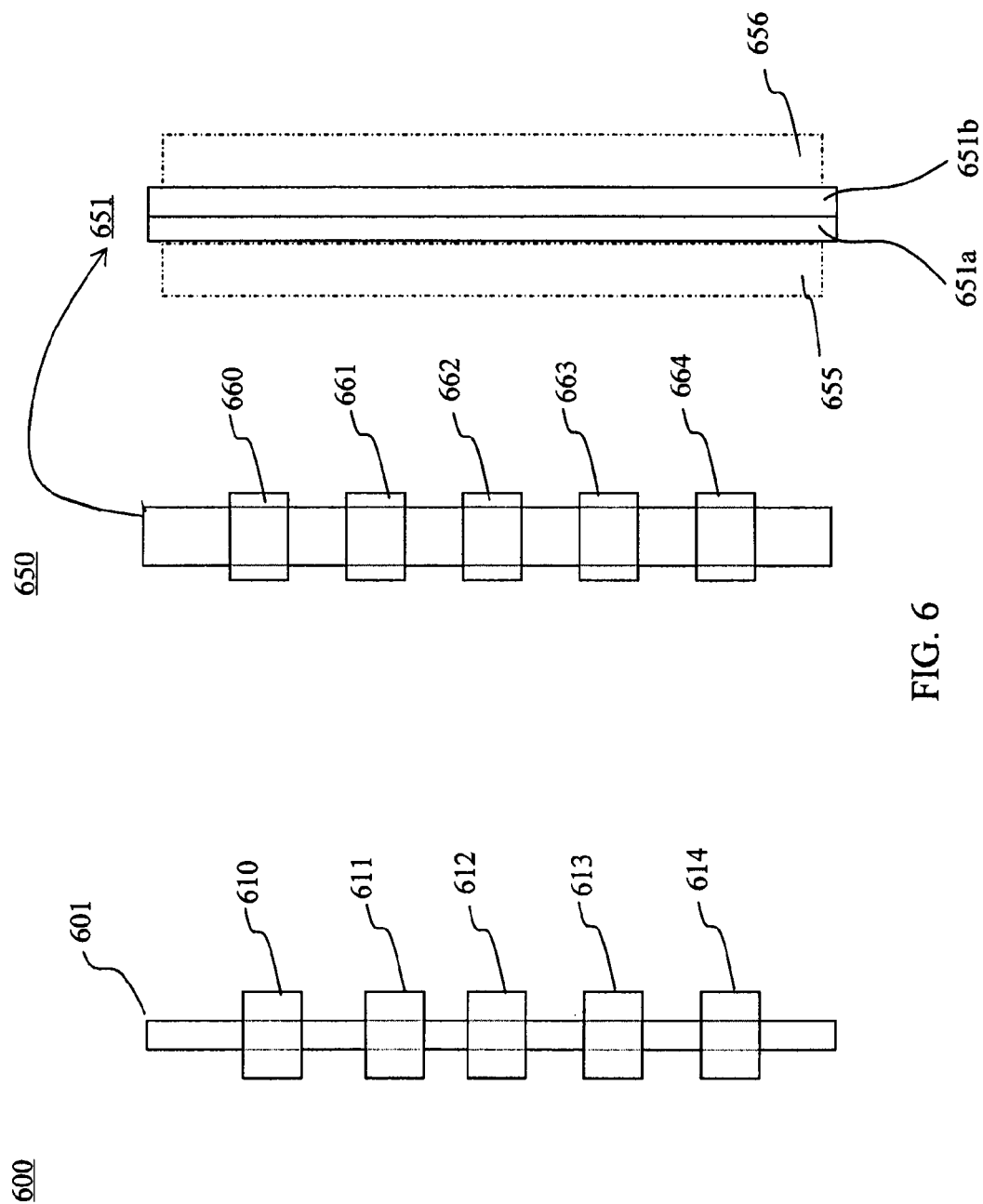


FIG. 6

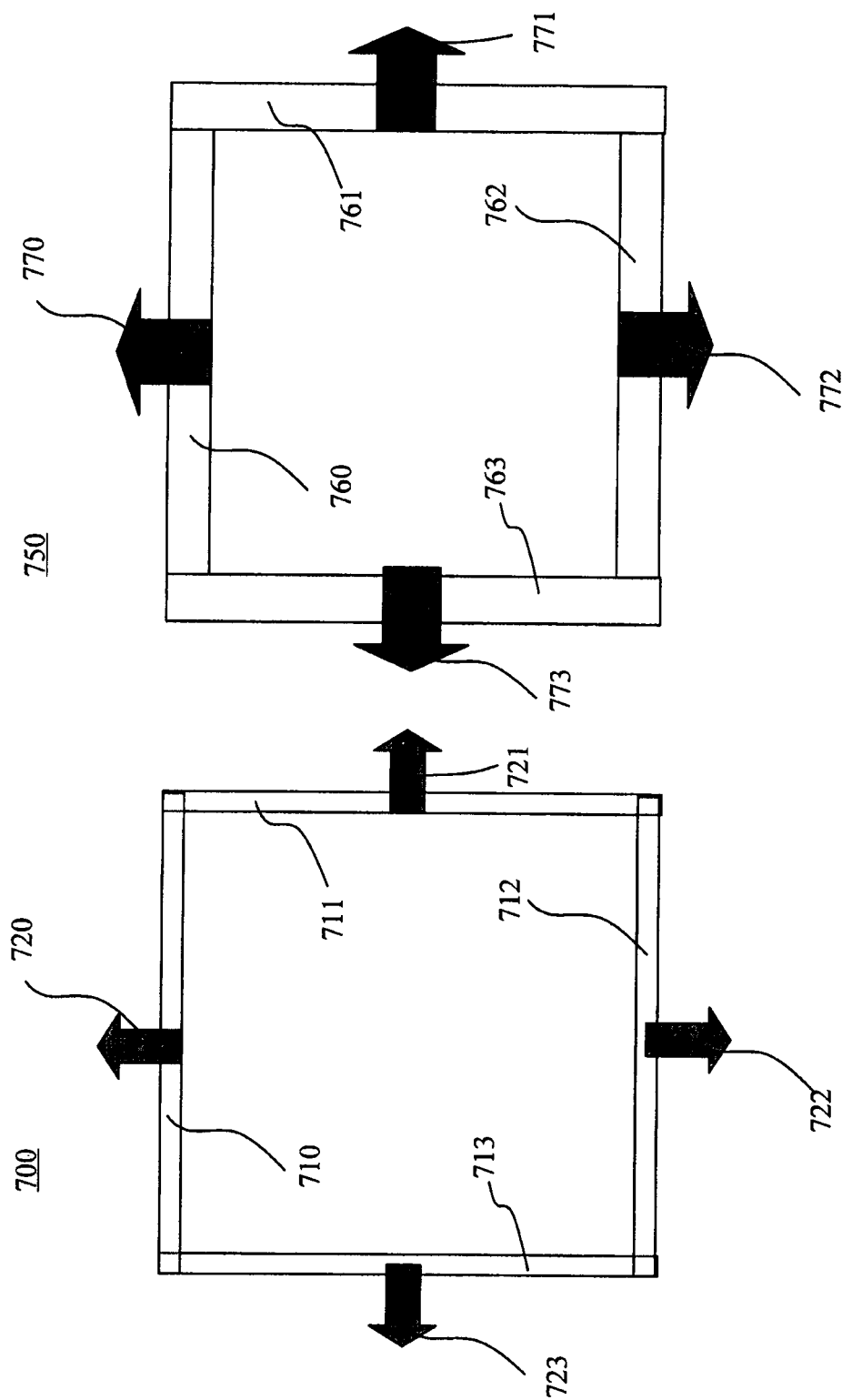


FIG. 7

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ADJUSTED FIN WIDTH IN INTEGRATED CIRCUITRY

This application is a Divisional of U.S. patent application Ser. No. 12/952,376, filed Nov. 23, 2010, which is hereby incorporated by reference in its entirety.

The present disclosure is related to the following commonly-assigned U.S. patent applications the entire disclosures of which are incorporated herein by reference: U.S. patent application Ser. No. 12/949,881 filed Nov. 19, 2010, entitled "Method for Forming Metrology Structures from Fins in Integrated Circuit"; and U.S. patent application Ser. No. 12/953,148 filed on Nov. 23, 2010, entitled "Devices and Method for Forming Fins in Integrated Circuitry."

BACKGROUND

The present disclosure relates generally to semiconductor manufacturing, and more particularly, to integrated circuit devices and methods for forming such devices.

The semiconductor industry continues to have goals of higher density, higher performance, and lower cost. Scaling of device size has been a major tool user to reach these goals. However, scaling beyond the 100 nm process technology node has several difficulties associated with it, such as gate-oxide thickness, source and drain doping depths, and current density. These difficulties have resulted in new device structures to improve the existing metal oxide semiconductor field effect transistor (MOSFET) devices. Some of these new device structures include multi-gate MOSFET devices. A fin field effect transistor (FinFET) is a kind of multi-gate device which has a channel formed as a vertical fin. Multiple gates are formed over and along the sides of the vertical fin. A FinFET allows for a range of channel lengths and provides a broader process window for gate structures. FinFET devices typically include high aspect-ratio semiconductor fins in which the channel and source/drain regions for the transistor are formed. The increased surface area of the channel and source/drain regions in a FinFET results in faster, more reliable and better-controlled semiconductor transistor devices. These advantages have found many new applications in various types of semiconductor devices.

A process for making a FinFET device uses stringent process control, including in the area of contact landing. For example, contact holes need to overlay with thin vertical fin channels or raised source/drain well-pick-up lines. Process control for contact landing gets even more difficult when horizontal and vertical gate lines co-exist in multi-gate FinFET structures.

As such, there is need for improving fin structures and other aspects of FinFET integrated circuitry.

SUMMARY

The present disclosure provides a method for forming fins in a semiconductor FinFET device. In one embodiment, the method includes growing a plurality of parallel mandrels on a surface of a semiconductor substrate, each mandrel having at least two laterally opposite sidewalls and a predetermined width. The method further includes forming a first type of spacers on the sidewalls of the mandrels, wherein the first type of spacers between two adjacent mandrels are separated by a gap. The predetermined mandrel width is adjusted to close the gap between the adjacent first type of spacers to form a second type of spacers. The mandrels are removed to form a first type of fins from the first type of spacers, and to

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form a second type of fins from spacers between two adjacent mandrels. The second type of fins are wider than the first type of fins.

In another embodiment, the method includes forming a first, second, and third mandrel on a surface of a semiconductor substrate, each mandrel having at least two laterally opposite sidewalls and a first width. The first and second mandrels are adjacent to each other, the third mandrel is a distance away from either the first or second mandrel. The method further includes forming spacers on the sidewalls of all three mandrels, wherein the spacers between the first and second adjacent mandrels are separated by a gap. The first width is adjusted to close the gap between the spacers between the first and second adjacent mandrels. The mandrels are removed to form a first fin from the spacers between the first and second mandrels, and a second fin from a spacer of the third mandrel.

The present disclosure also describes an integrated circuit device. In one embodiment, the device includes a substrate and first and second fins on the substrate. The first fin is about twice as wide as the second fin. The device also includes a gate dielectric layer on the first fin and a gate electrode on the gate dielectric layer. The gate electrode is in a direction perpendicular to a direction of the first fin.

BRIEF DESCRIPTION OF THE DRAWINGS

Aspects of the present disclosure are best understood from the following detailed description when read with the accompanying figures. It is emphasized that, in accordance with the standard practice in the industry, various features are not drawn to scale. In fact, the dimensions of the various features may be arbitrarily increased or reduced for clarity of discussion.

FIG. 1A is a cross section of an array of mandrels and spacers used in FinFET devices.

FIG. 1B illustrates the top view of the array of mandrels and spacers corresponding to FIG. 1A.

FIG. 1C is the top view of the array of fin structures resulted from the array of mandrels and spacers shown in FIG. 1A and FIG. 1B.

FIG. 2A and FIG. 2B are cross section and top views of an array of parallel mandrels and spacers when merged spacer technique is applied, in accordance with certain embodiments of the present disclosure.

FIG. 3A and FIG. 3B are cross section and top views of an array of wider fin structures resulted from the array of mandrels and merged spacers shown in FIG. 2A and FIG. 2B.

FIG. 4A is a top view of contact connections with an array of L-shaped and T-shaped spacers used in FinFET devices. FIG. 4B illustrates a cross sectional view of the contact connections with the L-shaped and T-shaped fin array, along the X-X' cut line shown in FIG. 4A.

FIG. 5A is a top view of contact connections with an array of L-shaped and T-shaped spacers used in FinFET devices when merged spacer technique is applied, and FIG. 5B is a cross sectional view of the contact connections with the L-shaped and T-shaped fin array, along the Y-Y' line shown in FIG. 5A, in accordance with some embodiments of the present disclosure.

FIG. 6 compares a contact connection structure having a thin fin structure and another contact connection structure having a wider fin structure when merged spacer technique is applied, in accordance with some embodiments of the present disclosure.

FIG. 7 compares an emitter ring of bipolar junction transistors (BJT) built on a thin fin structure and another emitter ring of BJT built on a broadened fin structure when merged spacer technique is applied, in accordance with various embodiments of the present disclosure.

DETAILED DESCRIPTION

It is to be understood that the following disclosure provides many different embodiments, or examples, for implementing different features of the invention. Specific examples of components and arrangements are described below to simplify the present disclosure. These are, of course, merely examples and are not intended to be limiting. Moreover, the formation of a first feature over or on a second feature in the description that follows may include embodiments in which the first and second features are formed in direct contact, and may also include embodiments in which additional features may be formed interposing the first and second features, such that the first and second features may not be in direct contact. Various features may be arbitrarily drawn in different scales for simplicity and clarity. In addition, the present disclosure may repeat reference numerals and/or letters in the various examples. This repetition is for the purpose of simplicity and clarity and does not in itself dictate a relationship between the various embodiments and/or configurations discussed. The specific embodiments discussed are merely illustrative and do not limit the scope of the invention.

Fin field effect transistors (FinFETs) use a substantially rectangular fin structure which can be formed in several ways. In a first method, bulk silicon on a substrate is etched into rectangular fin shape by first depositing a hardmask layer on the bulk silicon. The hardmask forms a pattern covering the top of the fins. The bulk silicon is then etched to form trenches between the regions covered by the hardmask layer. The trenches are formed into shallow trench isolation (STI) features by depositing a dielectric material, usually silicon oxide, into the trench. The dielectric material is usually deposited in excess to completely cover the fins and optionally the hardmask layer if not already removed. The dielectric material is planarized down to the top surface of the fin/hardmask, and then etched to a level below the top of the fin so that a portion of the fin protrudes above the STI.

In a second method, the STI features are formed first on bulk silicon material by depositing an STI layer and etching trenches into it. The bottoms of the trenches between the STI features are exposed bulk silicon. Silicon is then grown in the trenches to form the fins by using, for example, an epitaxial process. Once a desired fin height is reached, then the STI is etched to a level below the top of the fin to expose a portion of the fin. The bulk silicon material may be a silicon substrate or deposited silicon such as silicon-on-insulator (SOI) with a barrier oxide (BOX) layer between the SOI and the underlying silicon substrate.

Both methods above use a photomask process at the desired fin dimension, often at or beyond the limit of the current photolithography technology. With the increasing demand to reduce device size, a variation of the first method was developed, in which elongated mandrels are used as spacers at both lateral sides of mandrel as fins after the mandrels are removed. The mandrel/spacer process is described in FIG. 1A and FIG. 1B.

Referring to FIGS. 1A-1C, a semiconductor substrate 110, such as a silicon substrate, or a silicon on oxide substrate. The substrate includes an array of mandrels. Mandrels 121,

122, 123, 124, and 125 is formed by a photolithography and etch process. The mandrels are spaced at a pitch 101 and have a width 102. A conformal spacer material is then deposited around each of the mandrels 121, 122, 123, 124, and 125, forming a spacer array. In the present embodiment, the spacer array is made of a hardmask material, and spacer sidewalls 131, 132a, 132b, 133a, 133b, 134a, 134b, 135a, 135b, and 136 are thinner than the width of the mandrels 121, 122, 123, 124, and 125. In the present embodiment, the pitch and width of the mandrel array are selected such that facing sidewalls of a pair of adjacent mandrel structures are separated from each other at a distance on the order of the width 102 of a mandrel. As can be seen, mandrels 121, 122, 123, 124, and 125 are sandwiched between spacer sidewalls 131 and 132a, 132b and 133a, 133b and 134a, 134b and 135a, 135b and 136 respectively.

The mandrels 121, 122, 123, 124, and 125 between the spacers are then removed in a subsequent etching operation to leave just the spacers behind, now referred to as fin structures. It is understood that the fin structures can be used as a hardmask for etching the silicon layers below, forming additional fin structures. Using the mandrel/spacer method, the fin structures 131, 132a, 132b, 133a, 133b, 134a, 134b, 135a, 135b, and 136 are very thin and close together, and can be formed without a difficult lithography process. Thus formed fin structures have a width 152 at a pitch 151 (FIG. 1C), which can be half the mandrel pitch 101. For example, the mandrel pitch varies from 20 nm to 200 nm, the mandrel width varies from 10 nm to 100 nm, and the fin width varies from 5 nm to 80 nm. The vertical fin structures are the building blocks for forming gate channels for double, triple, and multiple gate transistors in a FinFET process.

It may further be a desire to form fin structures of different widths. For example, a number of circuit components may use various lateral dimensions for various vertical structures, which may benefit from multi-sized fin structures. Furthermore, it may be desired for the fin structures formed in the above mandrel and spacer process to provide relatively large contact landing areas on the top surface of a connection line. In addition, it may be desired to improve well-pick-up in source and drain structures, as well as improved emitter efficiency in bipolar junction transistor (BJT) integrated circuits.

A modification of the above-described method is discussed below to achieve one or more of the above-listed desires. It is further desired for the modification to maintain the fin density within the confines of existing transistor structures. Furthermore, it may be undesirable to require new photomasks to be made, especially for an existing product. Hence, it is desired to avoid creating new photomasks, and form FinFETs within the confines of the existing transistor structures so that layouts of other layers are not affected.

Referring now to FIGS. 2A-2B, a method of making fin structures in a semiconductor substrate 210, such as a silicon substrate or silicon on oxide substrate is provided. For the sake of reference, this method will be referred to as the spacer-merging process. An array of mandrels 221, 222, 223, 224, and 225 is formed by a photolithography and etch process. Based on device requirement for a specific fin dimension, the mandrel array is designed to have a pitch 201 and a width 202 that are appropriate to form the desired fins. A conformal spacer material is then deposited around the mandrels 221, 222, 223, 224, and 225. The conformal spacer array is usually made of a hardmask material. In addition, spacer sidewalls 231, 232a, 232b, 233a, 233b, 234a, 234b, 235a, 235b, and 236 are thinner than the width of the

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mandrels **221**, **222**, **223**, **224**, and **225**. The pitch and width of the mandrel array can be designed such that nearby facing sidewalls of a pair of adjacent mandrel structures actually touch and merge into one structure. As shown in FIG. 2B, mandrels **221**, **222**, **223**, **224**, and **225** are sandwiched between spacer sidewalls **231** and **232a**, **232b** and **233a**, **233b** and **234a**, **234b** and **235a**, **235b** and **236**, respectively. Facing sidewalls **232a** and **232b**, **233a** and **233b**, **234a** and **234b**, and **235a** and **235b** are located very closely to each other, or are touching each other respectively.

Now referring to FIGS. 3A-3B, the mandrel material between the spacers is then removed in a subsequent etching operation to leave just the spacers behind, which are now referred to as the desired fin structures. The fin structures **232**, **233**, **234**, and **235** are formed from joining the nearby spacers **232a** and **232b**, **233a** and **233b**, **234a**, and **234b** respectively. As shown in FIG. 3B the thus formed fins **232**, **233**, **234**, and **235** have a wider width **252** at a pitch **251**, which is the same as the mandrel pitch **201**. At the same time, fin structures **231** and **236** are not merged with other spacers; therefore fin structures **231** and **236** have their fin width unchanged. The pitch **251** is changed within the allowed range by the device layouts in the full process. For example, the mandrel pitch may vary from 20 nm to 200 nm, its width may vary from 10 nm to 100 nm, and the fin width varies from 5 nm to 180 nm. The wider vertical fin structures can be used for forming connector lines for well-pick-ups, for contact landing pads in Fin IC circuits, for BJT emitter channels, and other applications that desire wider fins.

Referring to FIGS. 4A-4B, an array of L-shaped and T-shaped spacers is provided. Horizontal fins **401**, **402**, **403** and vertical fins **404**, **405**, and **406** are fabricated using a mandrel and spacer process similar to that in FIG. 1A, FIG. 1B, and FIG. 1C. Fin **404** is an L-shaped fin, and **405** and **406** are T-shaped fins according to their shapes in the layout. Contacts **421** and **422** are overlaid on fins **404** and **406** respectively. Fins **404** and **406** each form a contact landing surface **421a** and **422a** as shown in FIG. 4B. The lateral dimension of fins **401**, **402**, and **403** form gate channels for FinFETs, therefore they may be appropriate and do not need any changes. However, lateral dimension of connection line fins **404** and **406** are too thin for forming good contact landing.

Referring to FIGS. 5A-5B, another array of L-shaped and T-shaped spacers is provided. Horizontal fins **501**, **502**, **503** and vertical fins **504** and **505** are fabricated using the spacer-merging process. Fin **504** is an L-shaped fin and **505** is a T-shaped fin according to their shapes in the layout. Contacts **521** and **522** are overlaid on fins **504** and **505** respectively. Fins **504** and **505** are lines each forming a contact landing surface **521a** and **522a** as shown in FIG. 5B. Block **550** in FIG. 5A is enlarged to illustrate an intermediate layout with a pair of adjacent mandrels **551** and **552** and their merged sidewall spacers **504a** and **504b** before contact **521** is overlaid on top. And FIG. 5B illustrates a cross sectional view of a contact connection with the array of L-shaped and T-shaped spacers, along the dashed Y-Y' cut line in FIG. 5A. Lateral dimension of fins **501**, **502**, and **503** remain narrow to form gate channels for FinFETs. The lateral dimension of connection line fins **504** and **505** are doubled from single fins **504a** and **504b**, resulting in improved contact landing areas to **521a** and **522a**.

Referring to FIG. 6, a contact connection structure **600** having a thin fin structure and a contact connection structure **650** having a wider fin structure are shown. The fin structures can be created using the merged spacer technique as discussed above. A narrower fin structure **601** forms con-

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nections with contacts **610**, **611**, **612**, **613**, and **614**, where contact landings are limited by the lateral width of fin line **601**. However, contact connection structure **650** has a wider fin structure **651** to provide contact landing areas for contacts **660**, **661**, **662**, **663**, and **664**. Block **651** in FIG. 6 illustrates an intermediate layout with a pair of adjacent mandrels **655** and **656** and their merged spacers **651a** and **651b** before contacts **660**, **661**, **662**, **663**, and **664** are overlaid on the top surface of line **651**. As a result, the lateral dimension of connection line fin **651** is doubled from the single fins **651a** and **651b** to form improved contact landing.

FIG. 7 compares different emitter ring layouts of bipolar junction transistors (BJT) built according to the two methods discussed above. A bipolar junction transistor is a collector-base-emitter three-terminal transistor having a charge flow due to bidirectional diffusion of charge carriers across junctions from two regions of different charge concentrations.

Layout **700**, formed by the method of FIG. 1, illustrates an emitter ring formed of four thin fin structure sides **710**, **711**, **712**, and **713**. Other transistor components built on the emitter ring are not shown. A BJT emitter is heavily doped to increase the emitter injection efficiency. For high current gain, most of the carriers injected into the emitter-base junction come from the emitter. Therefore, emitter injection currents **720**, **721**, **722**, and **723** in the integrated BJT circuits can be limited from the narrow emitter fins **710**, **711**, **712**, and **713** as fin dimension keeps on shrinking.

In layout **750**, formed by the spacer-merging process, emitter injection currents **770**, **771**, **772**, and **773** in the integrated BJT circuits are largely increased from the broadened emitter fins **760**, **761**, **762**, and **763**. The wider fins **760**, **761**, **762**, and **763** are formed with the merged spacer technique described above. As a result of the wider emitter fins, BJT emitter efficiency is improved in **750**.

Although the embodiments and its advantages have been described in detail, it should be understood that various changes, substitutions and alterations can be made herein without departing from the spirit and scope of the invention as defined by the appended claims. Moreover, the scope of the present application is not intended to be limited to the particular embodiments of the process, machine, manufacture, and composition of matter, means, methods and steps described in the specification. As one of ordinary skill in the art will readily appreciate from the disclosure of the present invention, processes, machines, manufacture, compositions of matter, means, methods, or steps, presently existing or later to be developed, that perform substantially the same function or achieve substantially the same result as the corresponding embodiments described herein may be utilized according to the present invention. Accordingly, the appended claims are intended to include within their scope such processes, machines, manufacture, compositions of matter, means, methods, or steps.

What is claimed is:

1. An integrated circuit device comprising:

a substrate;

a first connection line fin and a second connection line fin on the substrate, each extending a first length in a first direction defined by a respective first sidewall and an opposing second sidewall and each having a first width in a second direction defined by a respective first end and an opposing second end, wherein the second direction is perpendicular to the first direction;

a third fin and a fourth fin on the substrate, each of the third and fourth fin extending a second length in the second direction defined by a respective third sidewall and an opposing fourth sidewall and each having a

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- second width in the first direction defined by a third end and an opposing fourth end;
 wherein the first end of each of the first and second connection line fins directly interfaces with the third sidewall of the third fin;
 wherein the first width is about twice that of the second width;
 a first contact disposed on the first connection line fin, wherein a bottom face of the first contact interfaces the first connection line fin and the bottom face is wider than the first width;
 a second contact disposed on the second connection line fin, wherein a bottom face of the second contact interfaces the second connection line fin;
 a first channel of a first fin-type field effect transistor formed in the third fin; and
 a second channel of a second fin-type field effect transistor formed in the fourth fin.
2. The integrated circuit device of claim 1, further comprising:
 a dielectric layer over the first connection line fin;
 a hole in the dielectric layer; and
 the first contact providing an electrical connection to the first connection line fin and through the hole.
3. The integrated circuit device of claim 1, wherein the first connection line fin provides a well connection line.
4. The integrated circuit device of claim 1, wherein the second contact extends beyond a first edge and beyond a second edge of the second connection line fin.
5. A semiconductor device, comprising:
 a first fin having a length in a first direction and a width in a second direction, wherein the length of the first fin is greater than the width of the first fin;
 a second fin having a length in the second direction and a width in the first direction, wherein the second fin

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- length is greater than the second fin width, wherein the first fin and the second fin physically interface, the first direction is substantially perpendicular the second direction;
 a third fin parallel to the first fin and having a length in a first direction and a width in a second direction, wherein the length of the third fin is greater than the width of the third fin;
 a fourth fin having a length in the second direction and a width in the first direction, wherein the length of the fourth fin is greater than the width of the fourth fin and wherein the length of the fourth fin is substantially parallel the length of the second fin; and
 wherein the width of the first fin and the width of the third fin are approximately equal and each greater than the width of the second fin and the width of the fourth fin, the width of the second and fourth fins being approximately equal, wherein the width of the first fin is approximately two times the width of the second fin; and wherein an end of the first fin physically contacts a sidewall of the second fin and an end of the third fin physically interfaces the sidewall of the second fin;
 a contact structure formed on the first fin, wherein the contact structure extends over a first sidewall and a second sidewall of the first fin;
 a first channel of a first fin-type field effect transistor formed in the second fin; and
 a second channel of a second fin-type field effect transistor formed in the fourth fin.
6. The semiconductor device of claim 5, wherein the the sidewall of the third fin has a length that defines the length of the second fin.

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